with a tunable light source, projecting light having a specific wavelength and a specific intensity onto the semiconductor devices for a predetermined time so that irradiated electrons in defective ones of the semiconductor devices, in which a distance between a valence band and a conduction band has a lower value as compared with that of defect-free ones of the semiconductor devices, are transferred into the conduction band from the valence band.

10. The method according to claim 9, which comprises providing the semiconductor chips as wafer-level memory chips.

11. The method according to claim 9, which comprises constructing the tunable light source to regulate a frequency of the light in a continuously variable manner.

12. The method according to claim 9, which comprises constructing a wafer sampler providing a housing for the light source.

13. The method according to claim 9, which comprises:

providing a surface for positioning the semiconductor devices thereon; and

moveably disposing a component selected from the group consisting of the tunable light source and the surface to adjust a relative position between the tunable light source and the surface.

14. The method according to claim 9, which comprises providing the tunable light source with optical fibers having ends, the ends of the optical fibers for projecting the light onto the semiconductor devices.

15. The method according to claim 9, which comprises providing the semiconductor devices as memory chips having memory cells that have been written to.

16. The method according to claim 9, which comprises providing a voltage supply for supplying a voltage to the semiconductor devices during testing of the semiconductor devices. --